

GMBT4403

PNP EPITAXIAL PLANAR TRANSISTOR

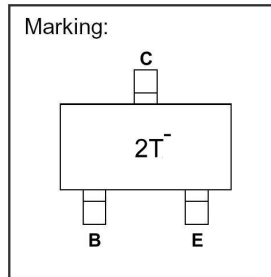
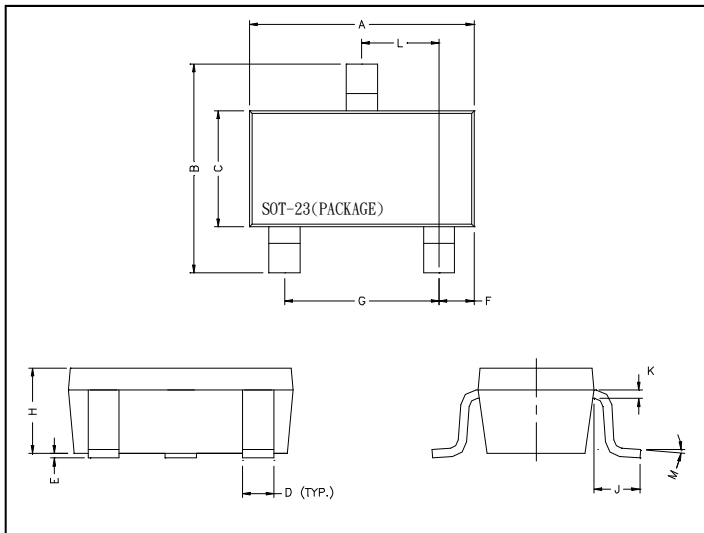
Description

The GMBT4403 is designed for general purpose applications requiring high breakdown voltage.

Features

- High DC Current Gain: 100-300 at 150mA
- Complementary to GMBT4401

Package Dimensions



| REF. | Millimeter | | REF. | Millimeter | |
|------|------------|------|------|------------|------|
| | Min. | Max. | | Min. | Max. |
| A | 2.70 | 3.10 | G | 1.90 | REF. |
| B | 2.40 | 2.80 | H | 1.00 | 1.30 |
| C | 1.40 | 1.60 | K | 0.10 | 0.20 |
| D | 0.35 | 0.50 | J | 0.40 | - |
| E | 0 | 0.10 | L | 0.85 | 1.15 |
| F | 0.45 | 0.55 | M | 0° | 10° |

Absolute Maximum Ratings at Ta = 25°C

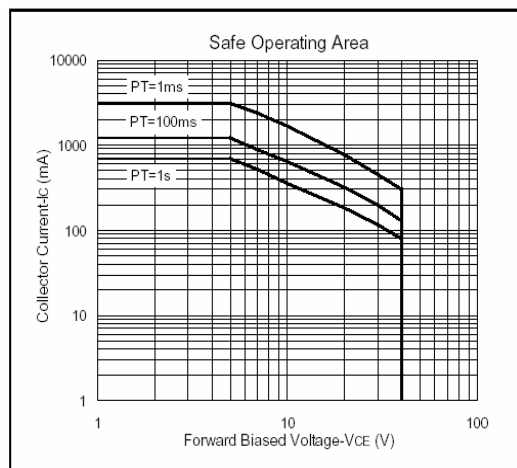
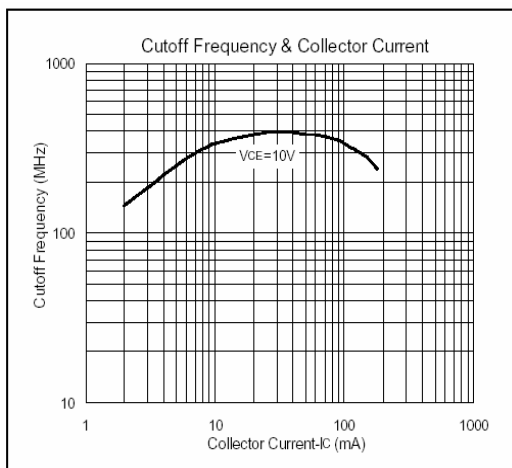
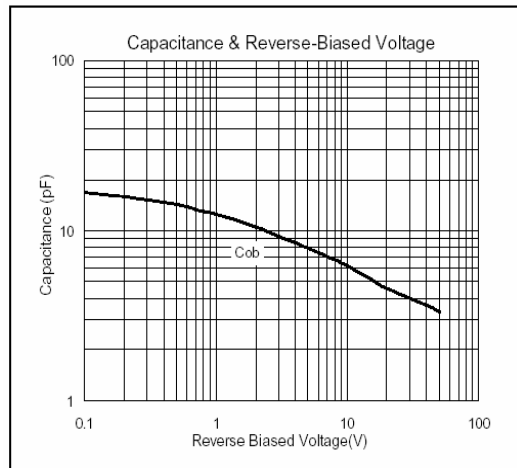
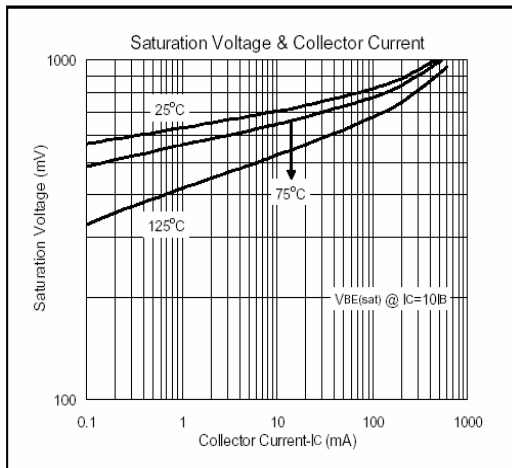
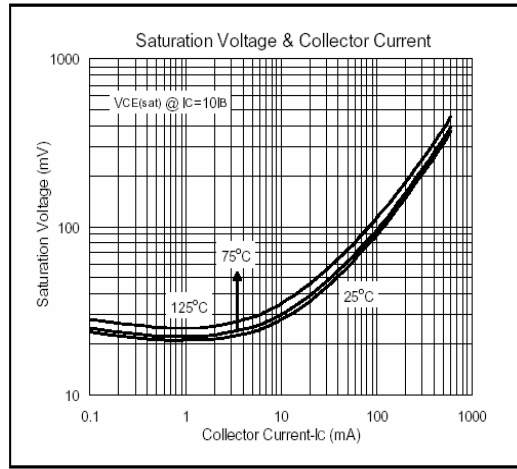
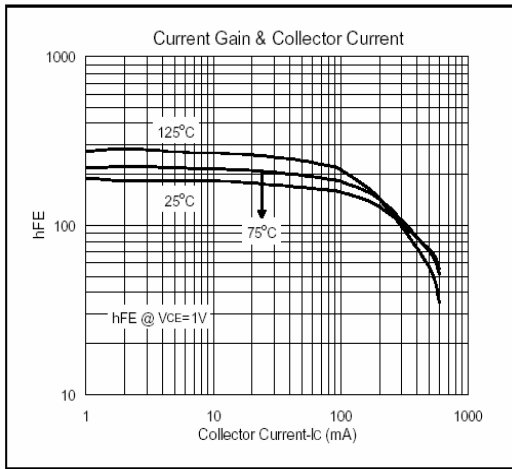
| Parameter | Symbol | Ratings | Unit |
|------------------------------|--------|------------|------|
| Junction Temperature | Tj | +150 | °C |
| Storage Temperature | Tstg | -55 ~ +150 | °C |
| Collector to Base Voltage | VCBO | -40 | V |
| Collector to Emitter Voltage | VCEO | -40 | V |
| Emitter to Base Voltage | VEBO | -5 | V |
| Collector Current | IC | -600 | mA |
| Total Power Dissipation | PD | 225 | mW |

Electrical Characteristics (Ta = 25°C, unless otherwise noted)

| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|------------|------|------|------|------|------------------------------|
| BVCBO | -40 | - | - | V | IC=-100uA |
| BVCEO | -40 | - | - | V | IC=-1mA |
| BVEBO | -5 | - | - | V | IE=-10uA |
| ICEX | - | - | -100 | nA | VCE=-35V, VBE=-0.4V |
| *VCE(sat)1 | - | - | -400 | mV | IC=-150mA, IB=-15mA |
| *VCE(sat)2 | - | - | -750 | mV | IC=-500mA, IB=-50mA |
| *VBE(sat)1 | - | - | -950 | mV | IC=-150mA, IB=-15mA |
| *VBE(sat)2 | - | - | -1.3 | V | IC=-500mA, IB=-50mA |
| *hFE1 | 30 | - | - | | VCE=-1V, IC=-0.1mA |
| *hFE2 | 60 | - | - | | VCE=-1V, IC=-1mA |
| *hFE3 | 100 | - | - | | VCE=-1V, IC=-10mA |
| *hFE4 | 100 | - | 300 | | VCE=-2V, IC=-150mA |
| *hFE5 | 20 | - | - | | VCE=-2V, IC=-500mA |
| fT | 200 | - | - | MHz | VCE=-10V, IC=-20mA, f=100MHz |
| Cob | - | - | 8.5 | pF | VCE=-10V, f=1MHz |

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Characteristics Curve



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